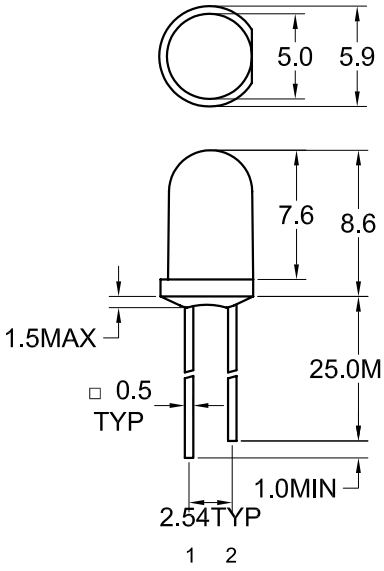
LIGITEK

NPN SILICON PHOTOTRANSISTOR LED LAMPS **LPT3333 SERIES**

Package Dimension



1.EMITTER
2.COLLECTOR

Note:1.All dimension are in millimeter tolerance is ±0.25mm unless otherwise noted
2.Specifications are subject to change without notice

Features

. High illumination sensitivity
. Stable characteristics
. Spectrally and mechanically matched with IR emitter

Description

The LPT3333 series are silicon nitride passivated NPN planar phototransistors with exceptionally stable characteristics and high illumination sensitivity the cases of LPT3333 are encapsulated in water clear plastic T1 3/4 package individuallt

• MAXIMUM RATINGS(Ta=25℃)

PARAMETER	MAXIMUM RATINGS	UNIT
Power Dissipation	100	mw
Collector-Emitter Voltage	30	V
Emitter-Collector Voltage	5	V
Operating Temperature	-50℃ TO +100℃	
Storage Temperature	-50℃ TO +100℃	
Lead Soldering Temperature(1.6mm From Body)	260℃ for 5 seconds	

• ELECTRICAL CHARACTERISTICS(Ta=25℃)

PARAMETER	SYMBOL	Min.	Typ.	Max.	UNIT	TEST CONDITION
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	30			V	Ic=1mA Ee=0mw/cm²
Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	5			V	I_E=100 μA Ee=0mw/cm²
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.4	V	Ic=0.5mA Ee=20mw/cm²
Rise Time	Tr		5		μs	V_{CE}=30V IC=800 μA, RL=1KΩ
Fall Time	Tf		5		μs	
Collector Dark Current	I_{CEO}			100	nA	V_{CE}=10V Ee=0mw/cm²
On State Collector Current	Ip(on)	1		2	mA	V_{CE}=5v Ee=1mw/cm² λP=940nm
		2		4	mA	
		4		8	mA	
		8			mA	